

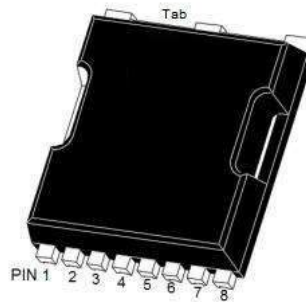
Features

- Uses MOT advanced double trench technology
- Low On-Resistance ($R_{DS(on)} \leq \text{m}\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- 100% avalanche tested
- Pb-free plating; RoHS compliant

Applications

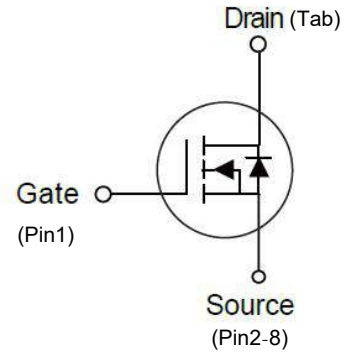
- Battery management
- Motor control and drive
- Synchronous rectification
- Switching applications

Pin configuration (Top view)



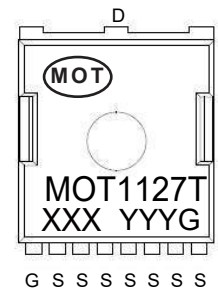
TOLL-8

Symbol



Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),typ.}$	2.4	mΩ
I_D	250	A



XXX=Lot Number
YYY = Year Week
G=Vth Range

Marking

Ordering information

Type/Ordering Code	Package	Marking	Packing&Qty.(pcs)
MOT1127T	TOLL-8	MOT1127T	2000/Reel

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Max	Unit
Drain-Source Voltage	V_{DS}	$T_C = 25^\circ\text{C}$	100	-	V
Gate-Source Voltage	V_{GS}	$T_C = 25^\circ\text{C}$	-	± 20	V
Drain Current (DC) *	I_D	$T_C = 25^\circ\text{C}, V_{GS} = 10\text{ V}$	-	250	A
		$T_C = 100^\circ\text{C}, V_{GS} = 10\text{ V}$	-	177	A
Drain Current (Pulsed)***	I_{DM}	$T_C = 25^\circ\text{C}, V_{GS} = 10\text{ V}$	-	1000	A
Drain power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$	-	357	W
Storage Temperature	T_{stg}		- 55	175	$^\circ\text{C}$
Junction Temperature	T_J		-	175	$^\circ\text{C}$
Continuous-Source Current	I_S	$T_C = 25^\circ\text{C}$	-	250	A
Single Pulsed Avalanche Energy	E_{AS}	$V_{DD} = 40\text{ V}, L = 1.0\text{ mH}$	-	1750	mJ
Thermal Resistance- Junction to Ambient**	$R_{\theta JA}$		-	32.8	$^\circ\text{C/W}$
Thermal Resistance- Junction to Case**	$R_{\theta JC}$		-	0.42	

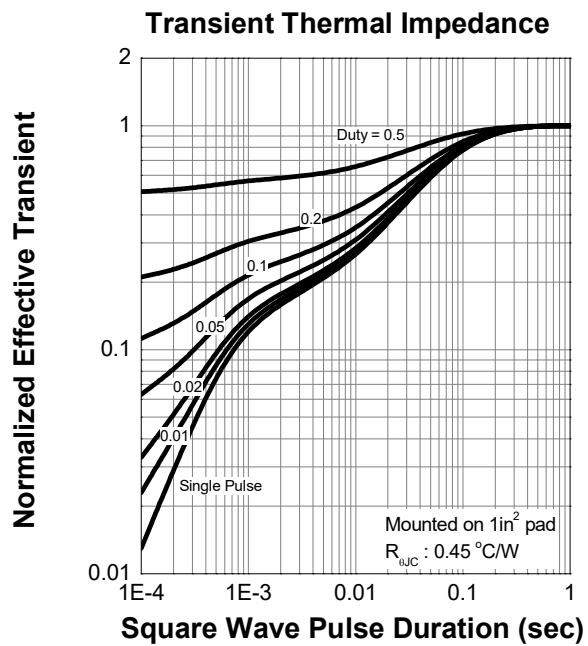
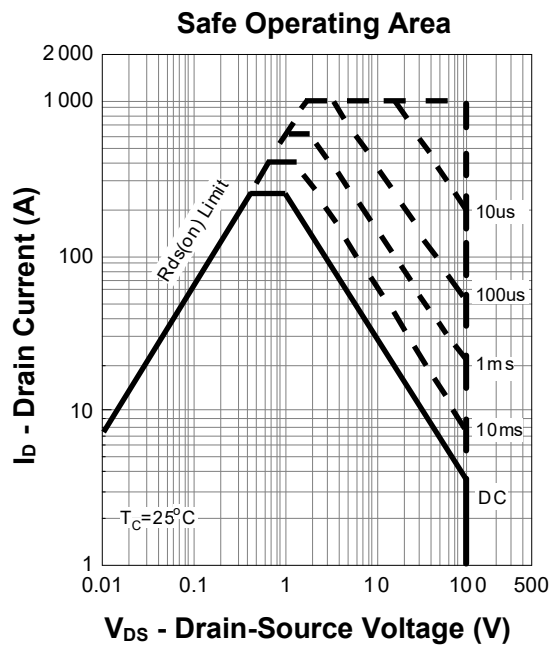
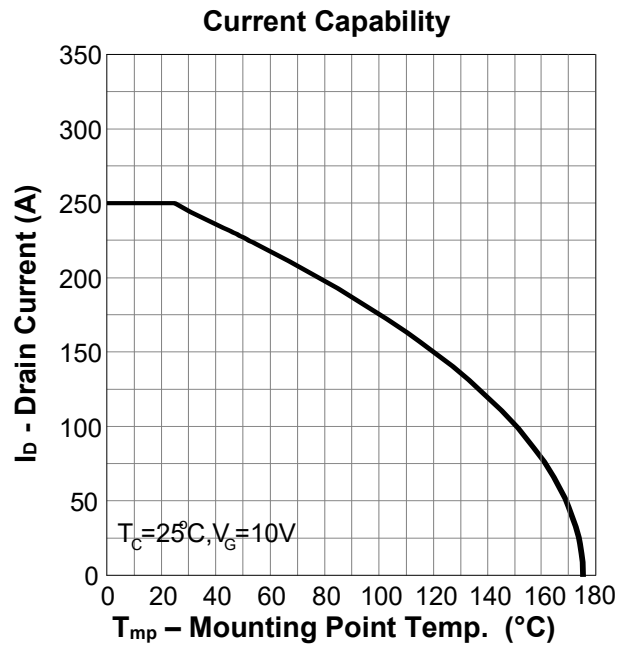
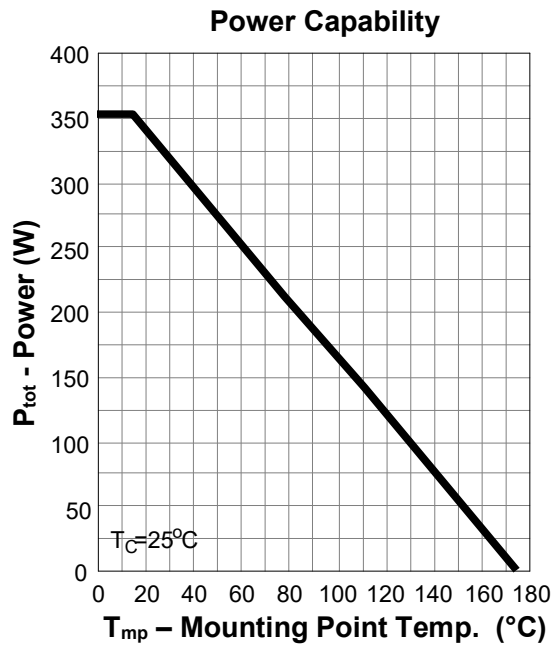
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _{DS} = 250 μA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	2	-	4	V
Drain Leakage Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ± 20 V, V _{DS} = 0 V	-	-	± 100	nA
On-State Resistance ^a	R _{DS(ON)}	V _{GS} = 10 V, I _D = 50 A	-	2.4	2.7	mΩ
Diode Characteristics						
Diode Forward Voltage ^a	V _{SD}	I _{SD} = 100 A, V _{GS} = 0 V	-	-	1.3	V
Reverse Recovery Time	t _{rr}	I _D = 100 A, V _{GS} = 0 V	-	80	-	nS
Reverse Recovery Charge	Q _{rr}	dI _{SD} /dt = 100 A/μs	-	195	-	nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V Frequency = 1 MHz	-	6100	-	pF
Output Capacitance	C _{oss}		-	2500	-	
Reverse Transfer Capacitance ^b	C _{rss}		-	125	-	
Turn-on Delay Time	t _{d(on)}	V _{DS} = 50 V, V _{GS} = 10 V, R _G = 4.5 Ω, R _L = 2.5 Ω, I _D = 100 A	-	32	-	nS
Turn-on Rise Time	t _r		-	40	-	
Turn-off Delay Time	t _{d(off)}		-	80	-	
Turn-off Fall Time	t _f		-	35	-	
Gate Charge Characteristics ^b						
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _{DS} = 20 A	-	131	-	nC
Gate-Source Charge	Q _{gs}		-	50	-	
Gate-Drain Charge	Q _{gd}		-	24.5	-	

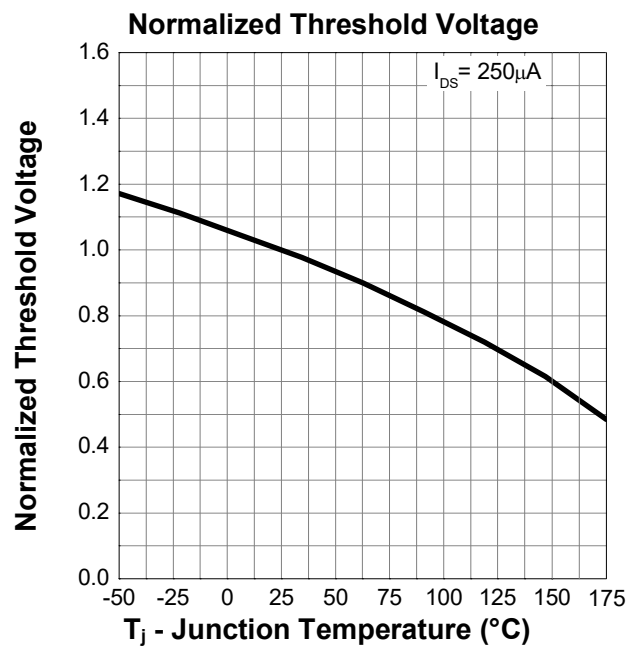
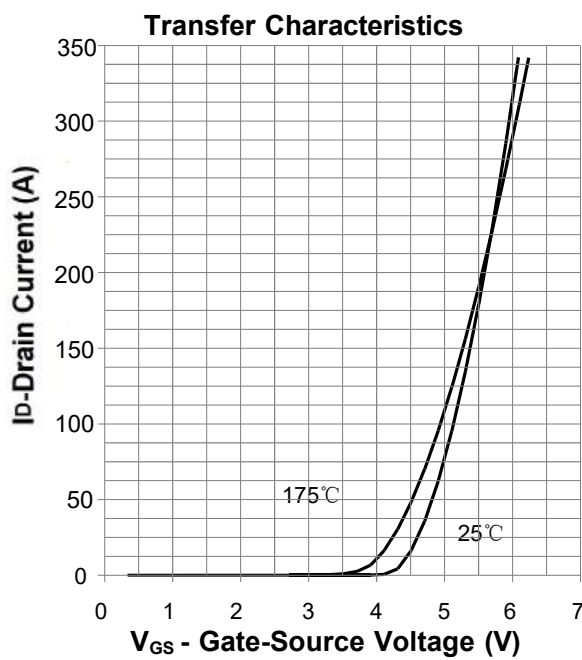
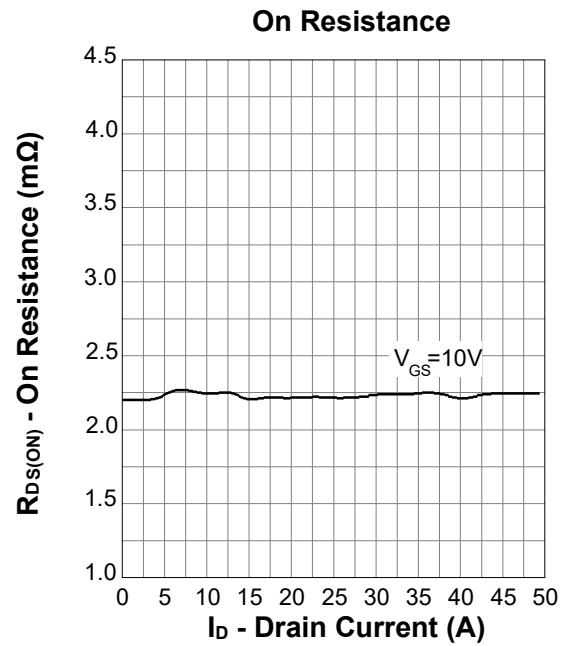
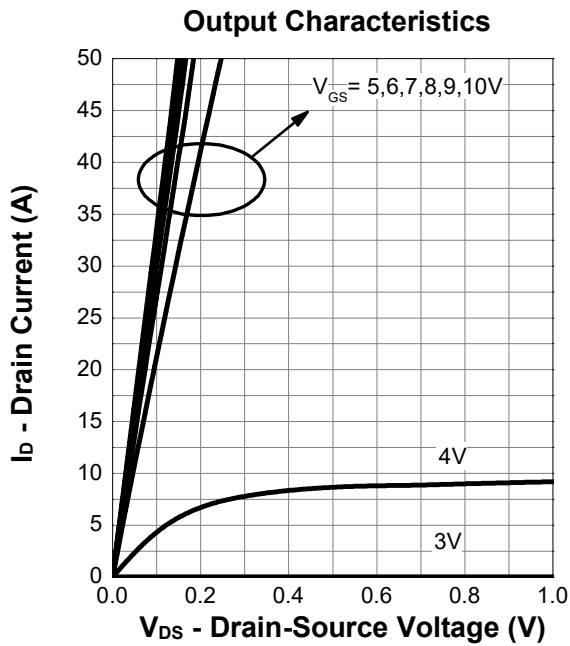
Notes :

- * Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- ** Surface Mounted on minimum footprint pad area.
- *** Limited by bonding wire
- a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%
- b : Guaranteed by design, not subject to production testing

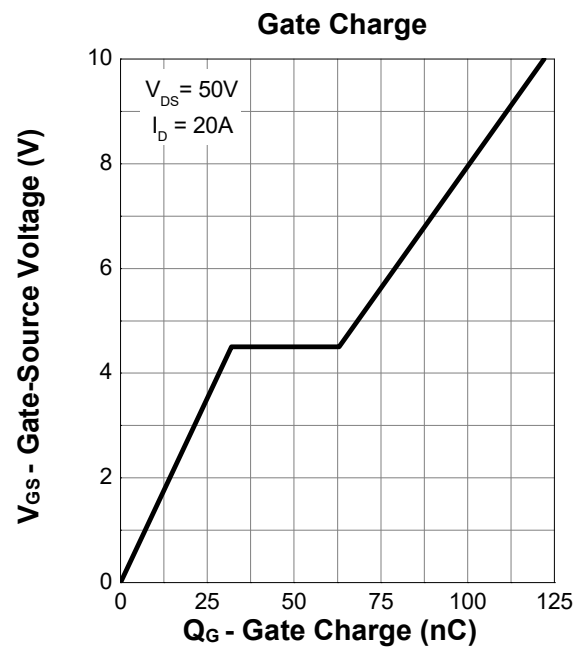
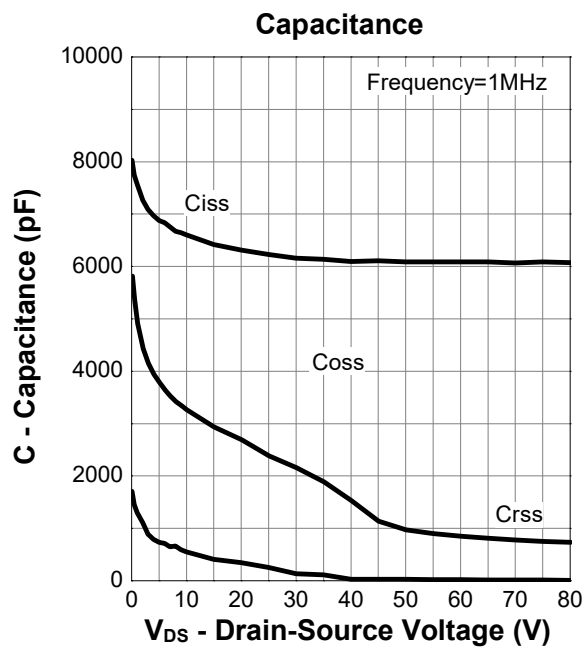
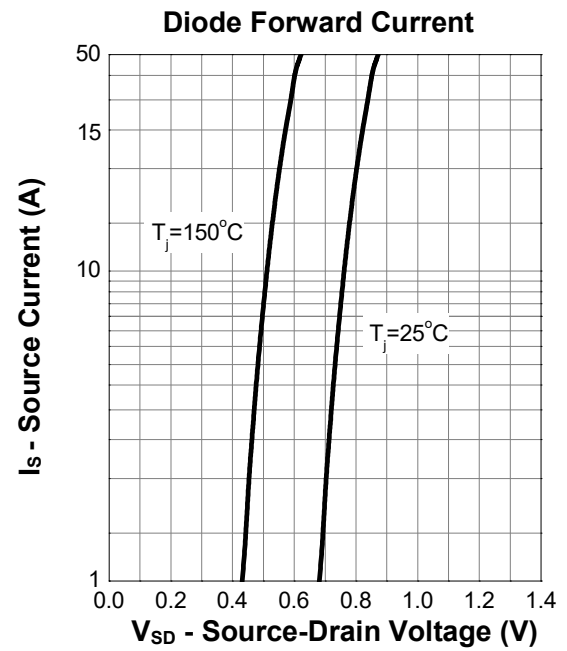
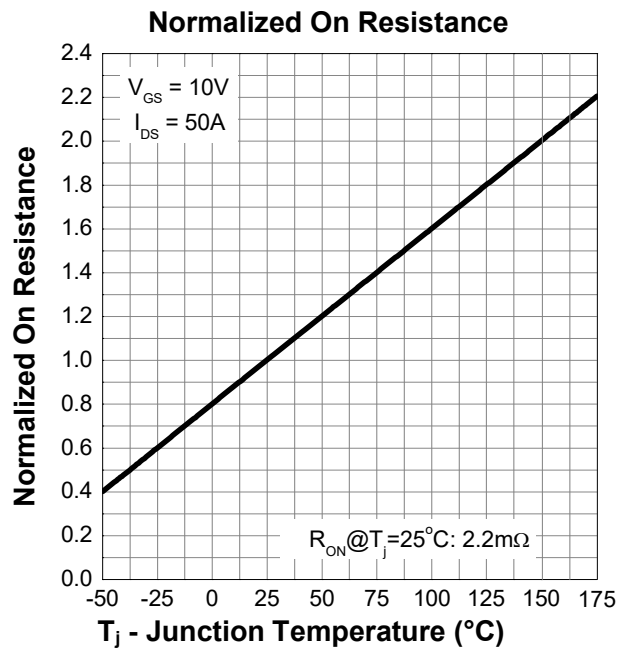
■ TYPICAL CHARACTERISTICS



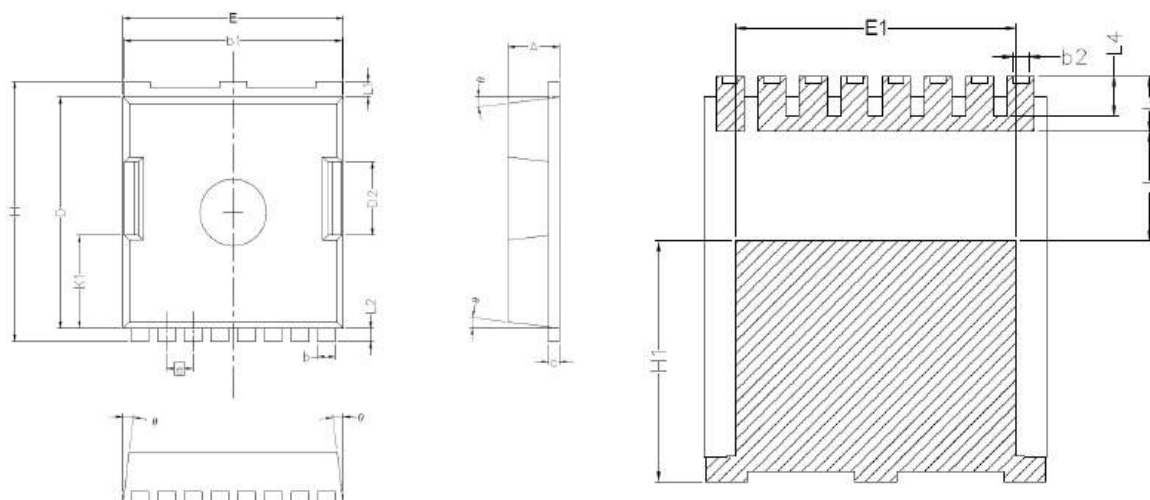
■ TYPICAL CHARACTERISTICS(Cont.)



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■ TOLL-8L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimesions In Millimeters	
	Min.	Max.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°

- The information contained herein is subject to change without notice.
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